



TP7F54M
 TP7F54M(H) **108-cel**
 395 - 415W
 10BB Half-cut Mono Perc



SYSTEM & PRODUCT CERTIFICATES

- IEC 61215 / IEC 61730 / UL 61730
- ISO 9001: 2015 Quality Management System
- ISO 14001: 2015 Environment Management System
- ISO 45001: 2018 Occupational Health and Safety Management Systems



PERFORMANCE WARRANTY



Linear Performance Warranty

KEY FEATURES



10BB Half-cut Cell Technology
 New circuit design, lower internal current, lower Rs loss
 Ga doped wafer, attenuation < 2% (1st year) / 0.55% (Linear)



2% more power generation, lower LCOE



2 times of industry standard Anti-PID test



IP68 Junction Box
 High waterproof level

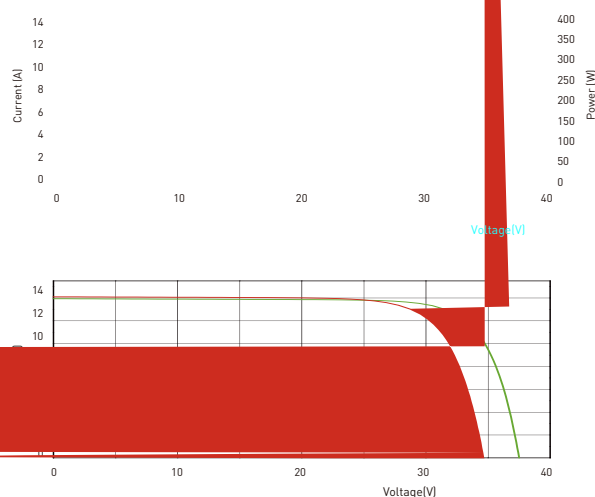
ELECTRICAL CHARACTERISTICS

	395	294	400	298	405	302	410	306	415	310
	30.85	28.8	31.05	29.0	31.24	29.2	31.43	29.3	31.64	29.6
	12.81	10.23	12.89	10.30	12.97	10.36	13.05	10.42	13.13	10.48
	36.75	34.6	37.00	34.8	37.25	35.1	37.50	35.3	37.75	35.5
	13.69	11.04	13.78	11.11	13.86	11.17	13.94	11.24	14.02	11.30
	20.20		20.50		20.70		21.00		21.30	

MECHANICAL CHARACTERISTICS

	Monocrystalline Silicon (10Busbar)
	108pcs in series (6*18)
	1722*1134*30mm (67.80*44.65*1.18inches)
	21.5kg (47.4lbs.)
	3.2mm AR Coating Tempered Glass
	Anodized Aluminium Alloy
	IP68, 3 Bypass Diodes
	4mm ² (IEC), 12AWG(UL) 350mm(+),250mm(-) or Customized Length
	T01/LJQ-3-CSY/MC4/MC4-EV02

I-V CURVE



	1000V/1500V/DC
	-40°C~+85°C
	25A
	Class

TECHNICAL DRAWINGS

TEMPERATURE CHARACTERISTICS

	-0.35%/°C
	-0.26%/°C
	+0.048%/°C
	43±2°C

PACKING CONFIGURATION

	36	36(USA)
	936	828



The specification and key features described in this datasheet may deviate slightly and are not guaranteed. Due to ongoing innovation, R&D enhancement, Suzhou Talesun Solar Technologies Co., Ltd. reserves the right to make any adjustment to the information described herein at any time without notice. Please always obtain the most recent version of the datasheet which shall be duly incorporated into the binding contract made by the parties governing all transactions related to the purchase and sale of the products described herein.